★ 100% EAS Guaranteed
★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

RoHS

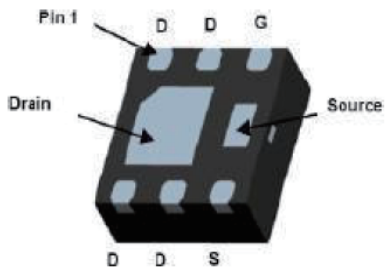
BVDSS	RDSON	ID
-30V	19mΩ	-10.0A

Description

The 30P10M is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 30P10M meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

DFN2X2-6L Pin Configuration



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-30		V
V_{GS}	Gate-Source Voltage	±20		
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ -10V[1]	-10		A
I_D@T_C=100°C		-8		
I_{DM}	Pulsed Drain Current[2]	-36		
EAS	Single Pulse Avalanche Energy[3]	25		mJ
I_{AS}	Avalanche Current	-8		A
P_D@T_C=25°C	Total Power Dissipation[4]	5		W
P_D@T_A=25°C		4.2	1.67	
T_{STG}	Storage Temperature Range	-55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150		

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	30	°C/W

Electrical Characteristics (T_J =25 °C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.022	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance2	V_{GS}=-10V , I_D=-15A	---	19	24	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	25	35	
$V_{GS(th)}$	Gate Threshold Voltage		-1	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	V_{GS}=V_{DS} , I_D =-250uA	---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±25V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	13	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-15A	---	48	---	nC
Q_{gs}	Gate-Source Charge		---	9.5	---	
Q_{gd}	Gate-Drain Charge		---	8	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-15A	---	12	---	ns
T_r	Rise Time		---	14	---	
$T_{d(off)}$	Turn-Off Delay Time		---	190	---	
T_f	Fall Time		---	90	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	1150	---	pF
C_{oss}	Output Capacitance		---	155	---	
C_{rss}	Reverse Transfer Capacitance		---	139	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current1,5	V_G=V_D=0V , Force Current	---	---	-10	A
I_{SM}	Pulsed Source Current2,5		---	---	-36	A
V_{SD}	Diode Forward Voltage2	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1. 1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,IAS=-38A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure1: Output Characteristics

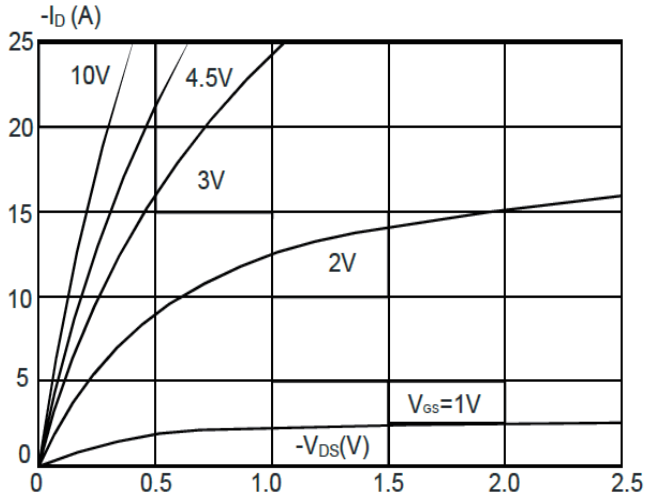


Figure 2: Typical Transfer Characteristics

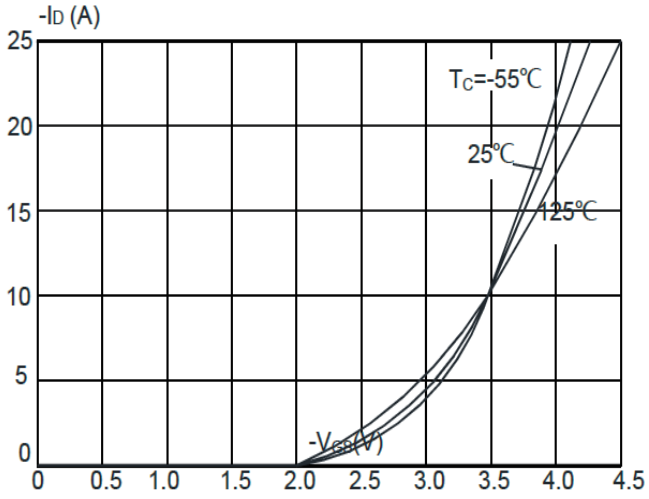


Figure 3:On-resistance vs. Drain Current

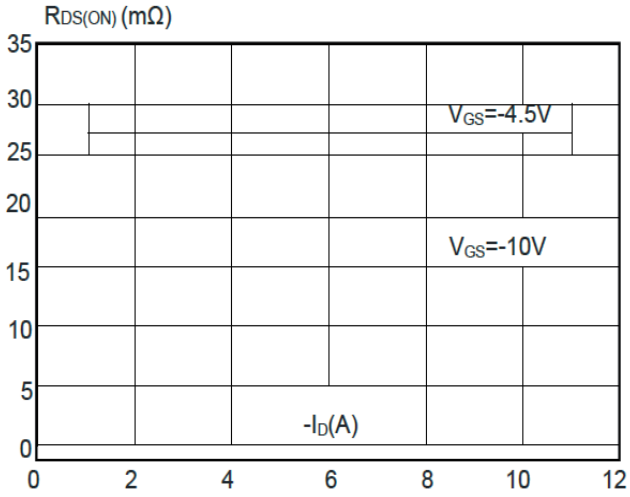


Figure 4: Body Diode Characteristics

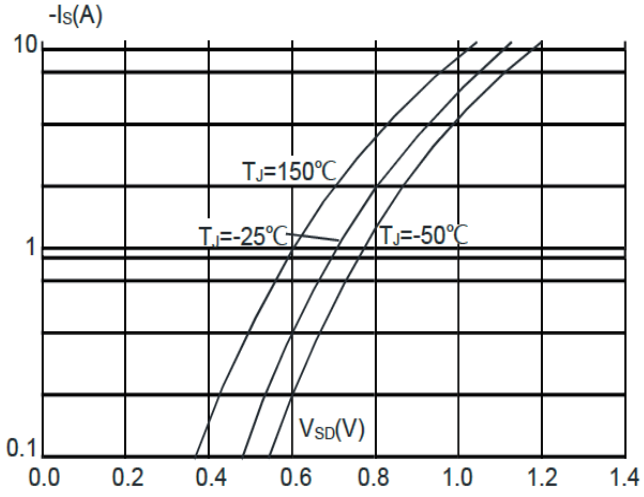


Figure 5: Gate Charge Characteristics

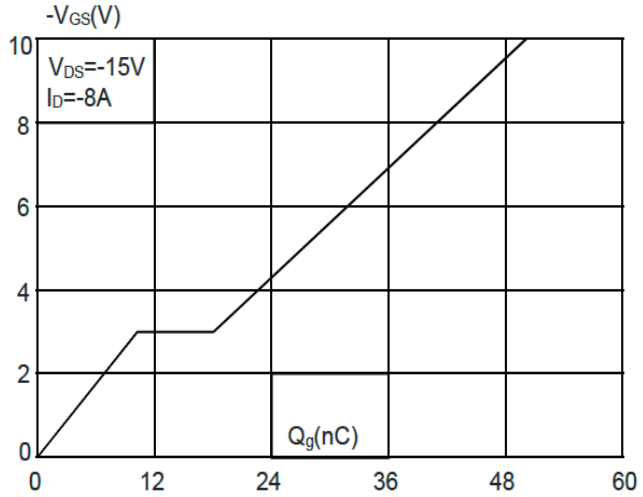
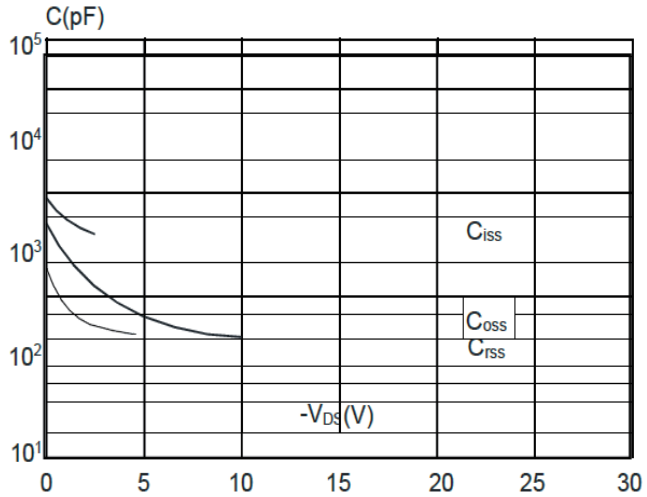


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage

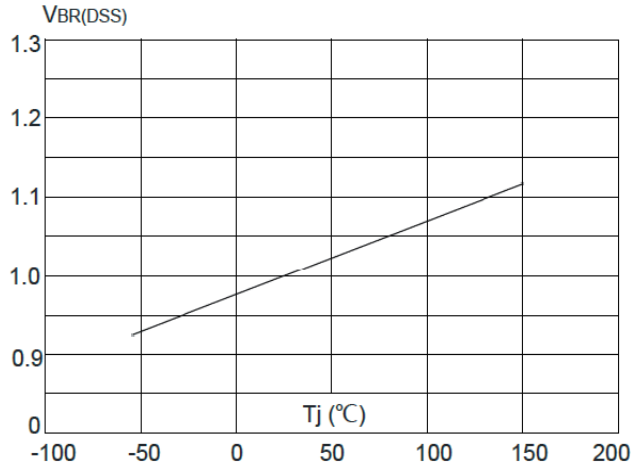


Figure 8:Normalized on Resistance vs.

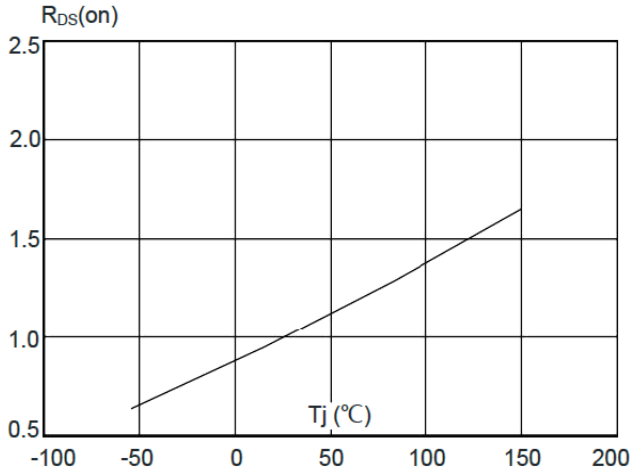


Figure 9: Maximum Safe Operating Area

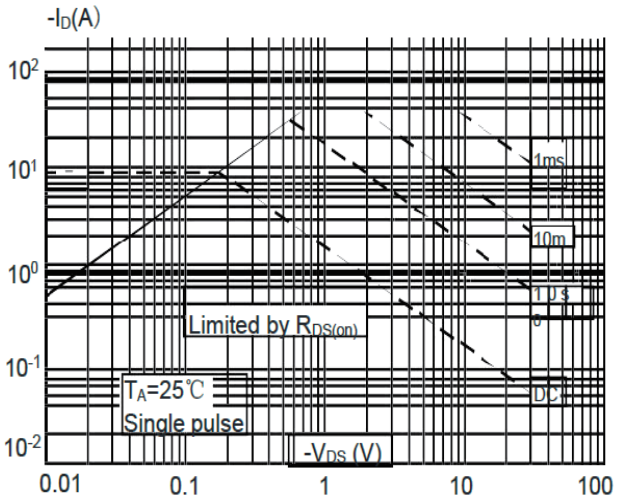


Figure 10: Maximum Continuous Drain Cu

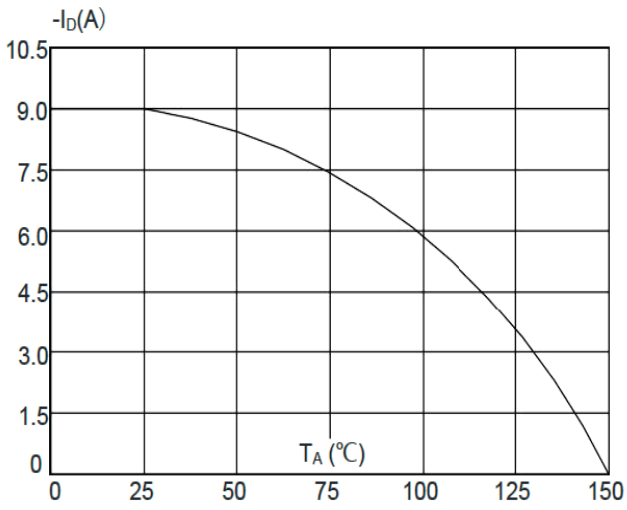
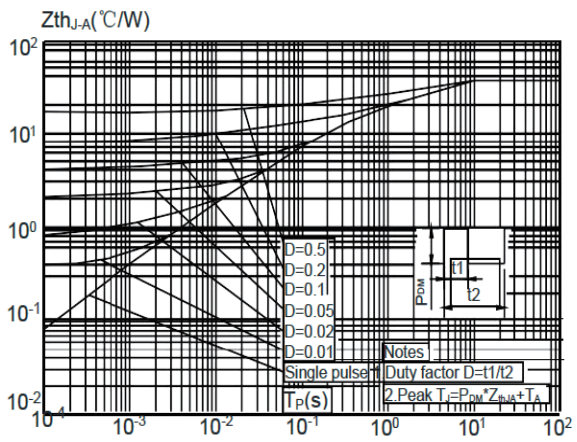


Figure 11: Maximum Effective Transient



Test Circuit

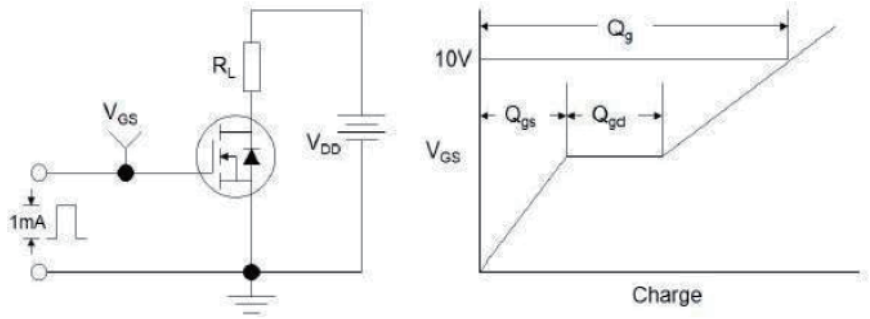


Figure1:Gate Charge Test Circuit & Waveform

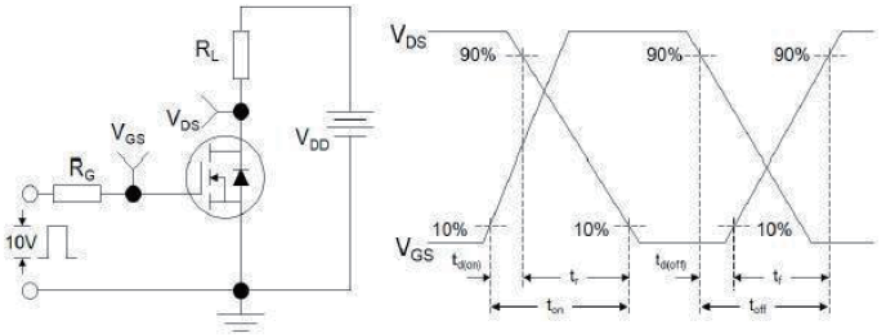


Figure 2: Resistive Switching Test Circuit & Waveforms

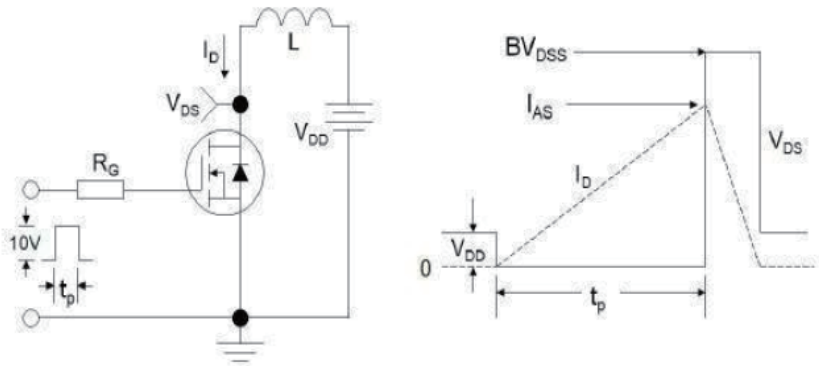
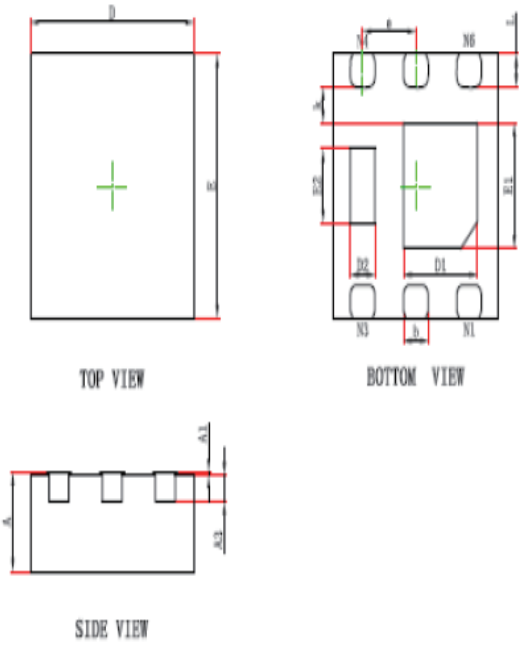


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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